# 2SD1385

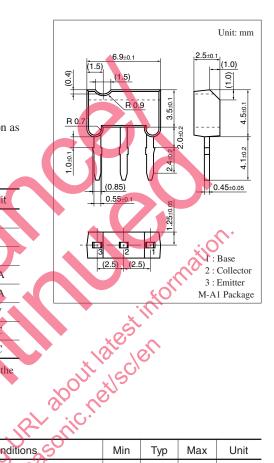
## Silicon NPN triple diffusion planar type

For low-frequency output amplification

#### Features

- High collector-base voltage (Emitter open)  $V_{CBO}$
- $\bullet$  Large collector power dissipation  $P_{C}$
- Low collector-emitter saturation voltage  $V_{CE(sat)}$
- M type package, allowing easy automatic and manual insertion as well as stand-alone fixing to the printed circuit board.

Absolute Maximum Ratings $T_a = 25^{\circ}C$							
Parameter	Symbol	Rating	Unit				
Collector-base voltage (Emitter open)	V <sub>CBO</sub>	400	V				
Collector-emitter voltage (Base open)	V <sub>CEO</sub>	400	V				
Emitter-base voltage (Collector open)	V <sub>EBO</sub>	5	V				
Collector current	I <sub>C</sub>	100	mA				
Peak collector current	I <sub>CP</sub>	200	mA				
Collector power dissipation *	P <sub>C</sub>	1	W				
Junction temperature	Tj	150	°C				
Storage temperature	T <sub>stg</sub>	-55 to +150	°C				

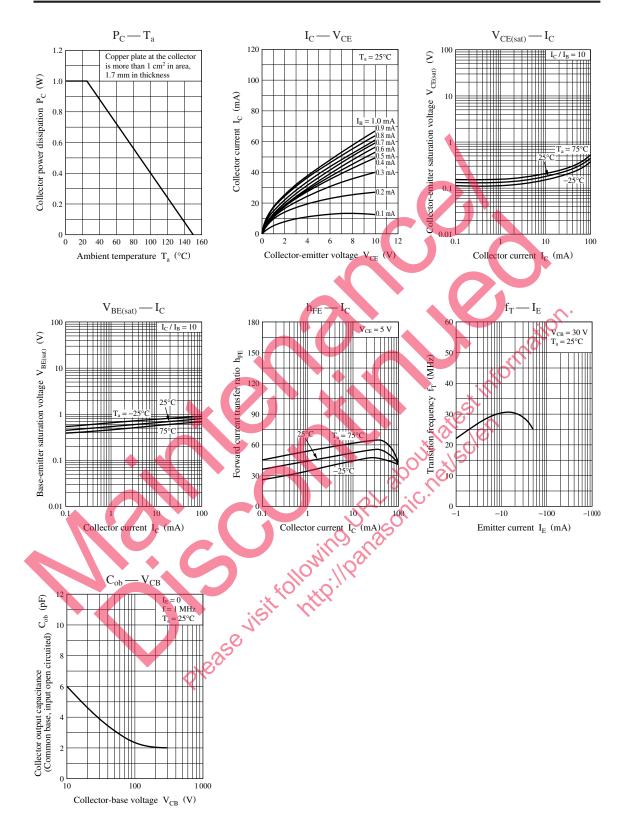


Note) \*: Printed circuit board: Copper foil area of 1 cm<sup>2</sup> or more, and the board thickness of 1,7 mm for the collector portion

### Electrical Characteristics $T_a = 25^{\circ}C \pm 3^{\circ}C$

Parameter	Symbol	Conditions S	Min	Тур	Max	Unit
Collector-base voltage (Emitter open)	V <sub>CBO</sub>	$I_{\rm C} = 100 \ \mu A, J_{\rm E} = 0$	400			V
Collector-emitter voltage (Base open)	V <sub>CEO</sub>	$I_{\rm C} = 500 \mu{\rm A},  I_{\rm B} = 0$	400			V
Emitter-base voltage (Collector open)	V <sub>EBO</sub>	$I_{\rm H} = 100 \ \mu A_{\rm c} A_{\rm C} = 0$	5			V
Forward current transfer ratio	h <sub>FE</sub>	$V_{CE} = 5 X, I_C = 30 \text{ mA}$	30			
Collector-emitter saturation voltage	V <sub>CE(sat</sub>	$I_{\rm C} = 50 \text{ mA}, I_{\rm B} = 5 \text{ mA}$			1.5	V
Base-emitter saturation voltage	VBE(sat)	$I_{C} = 50 \text{ mA}, I_{B} = 5 \text{ mA}$			1.5	V
Transition frequency	f <sub>T</sub>	$V_{CB} = 30 \text{ V}, I_E = -20 \text{ mA}, f = 200 \text{ MHz}$		40		MHz
Collector output capacitance	C <sub>ob</sub>	$V_{CB} = 30 \text{ V}, I_E = 0, f = 1 \text{ MHz}$			7	pF
(Common base, input open circuited)						

Note) Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.



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